

Features

- ESD Protected Up To 2KV (HBM)
- Trench LV MOSFET Technology
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

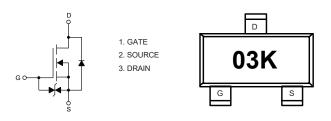
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 125°C/W Junction to Ambient^(Note2)

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Volltage		V _{GS}	±12	V	
Continuous Drain Current	T _A =25°C		8.0	Α	
	T _A =100°C	l _D	0.51		
Pulsed Drain Current ^(Note 3)		I _{DM}	3.2	Α	
Total Power Dissipation (Note 4)		P _D	1	W	

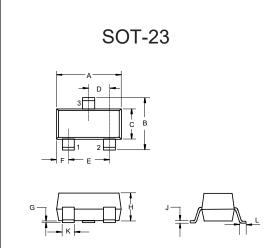
Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of R_{0JA} is measured with the device mounted on the minimum recommended pad size, in a still air environment with T_A =25°C.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.

Internal Structure and Marking Code

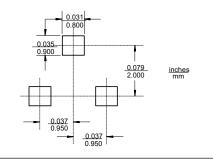


N-Channel MOSFET



DIMENSIONS					
DIM	INC	INCHES		М	NOTE
DIIVI	MIN	MAX	MIN	MAX	NOIL
Α	0.110	0.120	2.80	3.04	
В	0.083	0.104	2.10	2.64	
С	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
Е	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
Н	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

Suggested Solder Pad Layout





Electrical Characteristics @ 25°C (Unless Otherwise Specified)

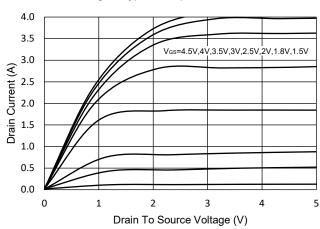
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	30			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±10	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	μΑ	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{D}=250\mu A$	0.6	1.0	1.3	V	
Dunin Course On Braintan		V _{GS} =4.5V, I _D =0.5A		340	510	mΩ	
Drain-Source On-Resistance	$R_{DS(on)}$	V _{GS} =2.5V, I _D =0.3A		435	660		
Forward Tranconductance	g _{FS}	V _{DS} =5V, I _D =0.8A		1.8		S	
Gate Resistance	R_g	f=1 MHz, Open drain		197		Ω	
Diode Characteristics	1			·		1	
Continuous Body Diode Current	Is				0.8	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =0.5A			1.2	V	
Reverse Recovery Time	t _{rr}	I _F =0.5A,di/dt=100A/μs		5.9		ns	
Reverse Recovery Charge	Q _{rr}	- 1 _F =0.5Α,α//αί=100Α/μs		2		nC	
Dynamic Characteristics							
Input Capacitance	C _{iss}			34.6			
Output Capacitance	C _{oss}	V _{DS} =15V,V _{GS} =0V,f=1MHz		6.2		pF	
Reverse Transfer Capacitance	C _{rss}			3.9		1	
Total Gate Charge	Q_g			0.64			
Gate-Source Charge	Q _{gs}	V _{DS} =15V,V _{GS} =4.5V,I _D =0.5A		0.09		nC	
Gate-Drain Charge	Q_{gd}			0.17			
Turn-On Delay Time	t _{d(on)}			8.2			
Turn-On Rise Time	t _r	V _{DD} =15V,V _{GS} =4.5V ,		23.3			
Turn-Off Delay Time	t _{d(off)}	$R_G=3\Omega$, $I_D=0.5A$		34.2		ns	
Turn-Off Fall Time	t _f			31.5			

4.5



Curve Characteristics

Fig.1 - Typical Output Characteristics



4.0 3.5 3.0 (X) 25°C 150°C 1.0

0.5

0.0

0.5

Fig.2 - Transfer Characteristic

Fig.3 - $R_{\rm DS(ON)}$ - $V_{\rm GS}$

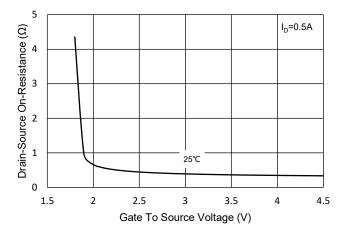


Fig.4 - R_{DS(ON)} - I_D

Gate To Source Voltage (V)

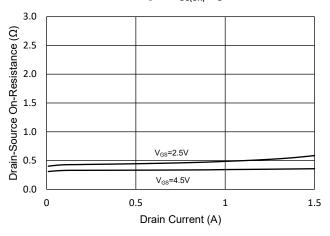


Fig.5 - Capacitance Characteristics

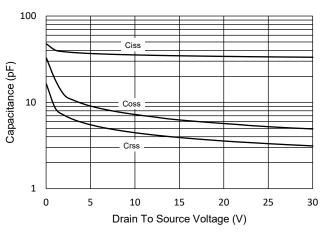
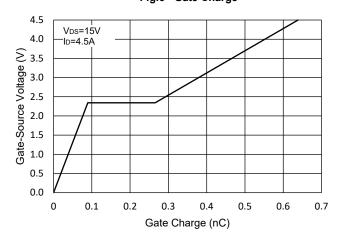


Fig.6 - Gate Charge





Curve Characteristics

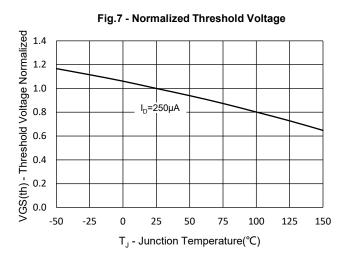


Fig.8 - Normalized On Resistance Characteristics

2.0
1.8
VGS=4.5V
ID= 0.5A

Fig.9 - I_S - V_{SD}

10

V_{GS}=0V

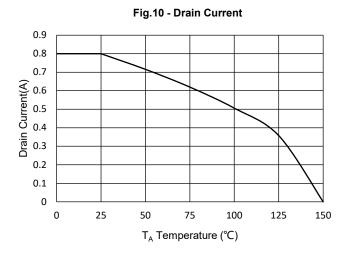
1 150°C

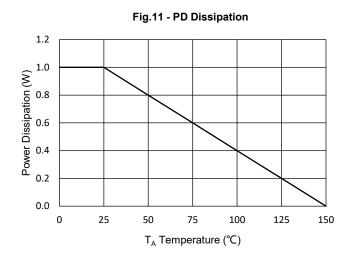
25°C

0.01

0.0 0.2 0.4 0.6 0.8 1.0 1.2

Source To Drain Voltage (V)







Curve Characteristics

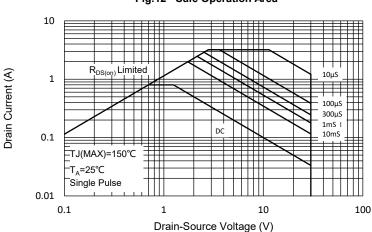
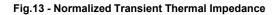
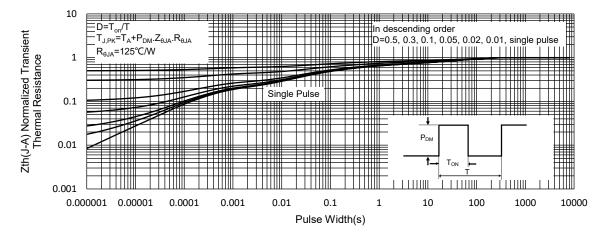


Fig.12 - Safe Operation Area







Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:3Kpcs/Reel

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